MMDT4413

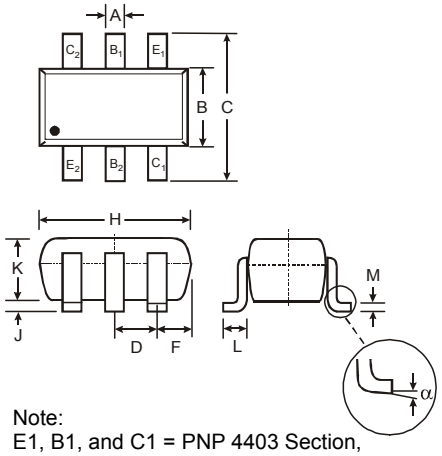
COMPLEMENTARY NPN / PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

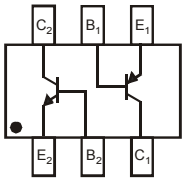
- Complementary Pair
- One 4401-Type NPN,
  One 4403-Type PNP
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 3)**
- **"Green" Device (Note 4 and 5)**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 6
- Ordering & Date Code Information: See Page 6
- Weight: 0.006 grams (approximate)



Note:
E1, B1, and C1 = PNP 4403 Section,
E2, B2, and C2 = NPN 4401 Section.
Type marking indicates orientation



SOT-363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings, Total Device @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 1, 2)	P_d	200	mW
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range		T_j, T_{STG}	-55 to +150	°C

Maximum Ratings, NPN 4401 Section @T_A = 25°C unless otherwise specified

Characteristic		Symbol	NPN4401	Unit
Collector-Base Voltage		V_{CBO}	60	V
Collector-Emitter Voltage		V_{CEO}	40	V
Emitter-Base Voltage		V_{EBO}	6.0	V
Collector Current - Continuous	(Note 1)	I_C	600	mA

Maximum Ratings, PNP 4403 Section @T_A = 25°C unless otherwise specified

Characteristic		Symbol	PNP4403	Unit
Collector-Base Voltage		V_{CBO}	-40	V
Collector-Emitter Voltage		V_{CEO}	-40	V
Emitter-Base Voltage		V_{EBO}	-5.0	V
Collector Current - Continuous	(Note 1)	I_C	-600	mA

Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. Maximum combined dissipation.
3. No purposefully added lead.
4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
5. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

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Electrical Characteristics, NPN 4401 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	—	V	I_C = 100μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	I_C = 1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	I_E = 100μA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	100	nA	V_{CE} = 35V, $V_{EB(OFF)}$ = 0.4V
Base Cutoff Current	I_{BL}	—	100	nA	V_{CE} = 35V, $V_{EB(OFF)}$ = 0.4V
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h_{FE}	20 40 80 100 40	— — — 300 —	—	I_C = 100μA, V_{CE} = 1.0V I_C = 1.0mA, V_{CE} = 1.0V I_C = 10mA, V_{CE} = 1.0V I_C = 150mA, V_{CE} = 1.0V I_C = 500mA, V_{CE} = 2.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.40 0.75	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.75 —	0.95 1.2	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}	—	6.5	pF	V_{CB} = 5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{eb}	—	30	pF	V_{EB} = 0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	1.0	15	kΩ	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.1	8.0	x 10^{-4}	
Small Signal Current Gain	h_{fe}	40	500	—	
Output Admittance	h_{oe}	1.0	30	μS	
Current Gain-Bandwidth Product	f_T	250	—	MHz	V_{CE} = 10V, I_C = 20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	15	ns	V_{CC} = 30V, I_C = 150mA, $V_{BE(off)}$ = 2.0V, I_{B1} = 15mA
Rise Time	t_r	—	20	ns	
Storage Time	t_s	—	225	ns	V_{CC} = 30V, I_C = 150mA, I_{B1} = I_{B2} = 15mA
Fall Time	t_f	—	30	ns	

Notes: 6. Short duration pulse test used to minimize self-heating effect.

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Electrical Characteristics, PNP 4403 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40	—	V	I_C = -100μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40	—	V	I_C = -1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0	—	V	I_E = -100μA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	-100	nA	V_{CE} = -35V, $V_{EB(OFF)}$ = -0.4V
Base Cutoff Current	I_{BL}	—	-100	nA	V_{CE} = -35V, $V_{EB(OFF)}$ = -0.4V
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h_{FE}	30 60 100 100 20	— — — 300 —	—	I_C = -100μA, V_{CE} = -1.0V I_C = -1.0mA, V_{CE} = -1.0V I_C = -10mA, V_{CE} = -1.0V I_C = -150mA, V_{CE} = -2.0V I_C = -500mA, V_{CE} = -2.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.40 -0.75	V	I_C = -150mA, I_B = -15mA I_C = -500mA, I_B = -50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.75 —	-0.95 -1.30	V	I_C = -150mA, I_B = -15mA I_C = -500mA, I_B = -50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}	—	8.5	pF	V_{CB} = -10V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{eb}	—	30	pF	V_{EB} = -0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	1.5	15	kΩ	V_{CE} = -10V, I_C = -1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.1	8.0	x 10^{-4}	
Small Signal Current Gain	h_{fe}	60	500	—	
Output Admittance	h_{oe}	1.0	100	μS	
Current Gain-Bandwidth Product	f_T	200	—	MHz	V_{CE} = -10V, I_C = -20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	15	ns	V_{CC} = -30V, I_C = -150mA, $V_{BE(off)}$ = -2.0V, I_{B1} = -15mA
Rise Time	t_r	—	20	ns	
Storage Time	t_s	—	225	ns	V_{CC} = -30V, I_C = -150mA, I_{B1} = I_{B2} = -15mA
Fall Time	t_f	—	30	ns	

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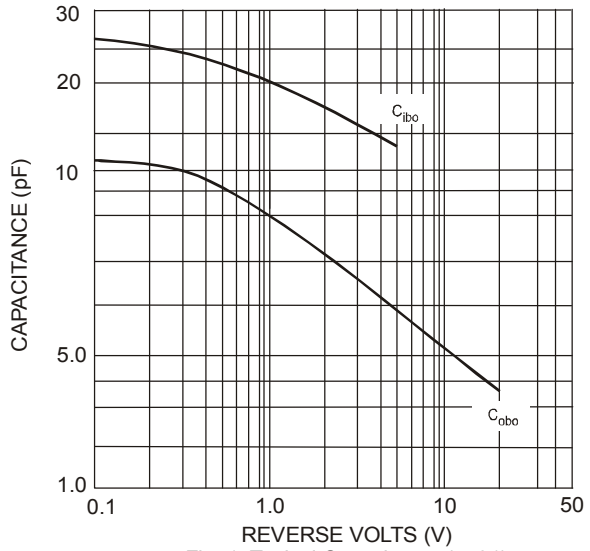


Fig. 1 Typical Capacitance (4401)

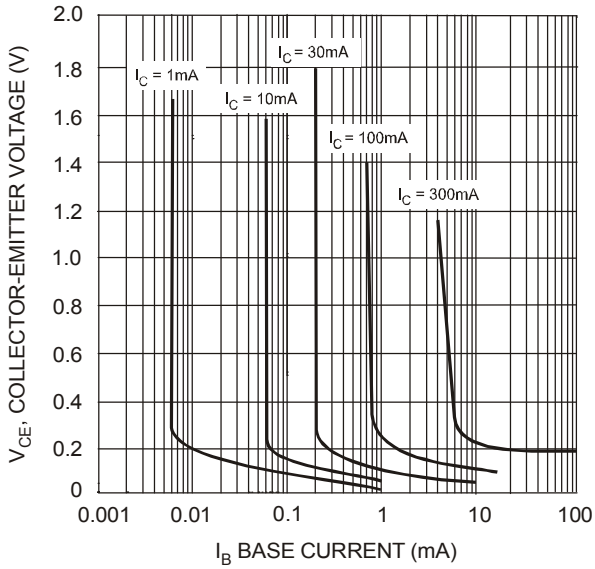


Fig. 2 Typical Collector Saturation Region (4401)

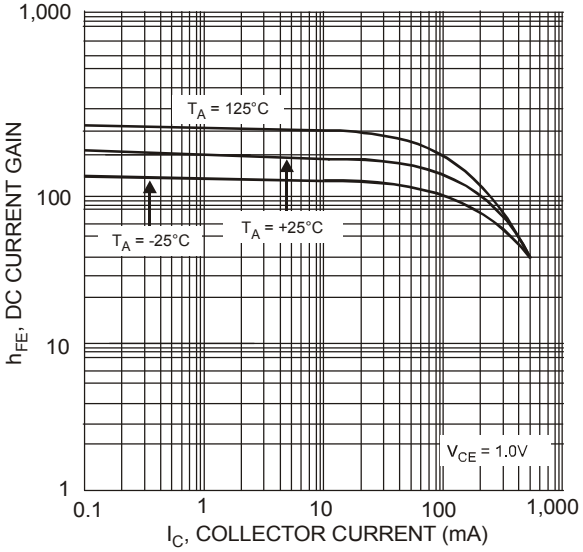


Fig. 3 Typical DC Current Gain vs. Collector Current (4401)

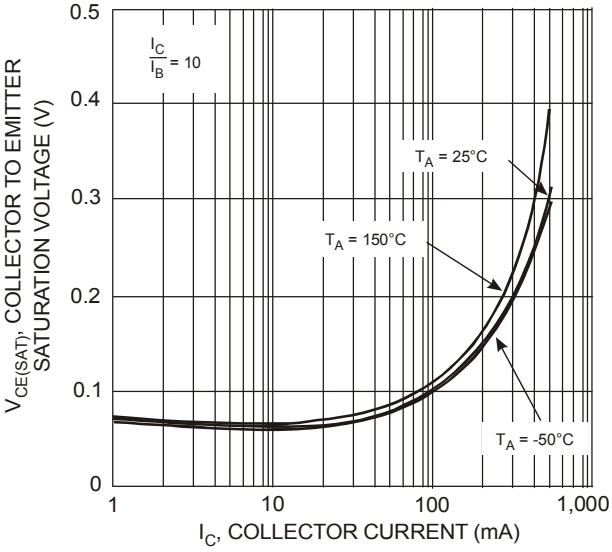


Fig. 4 Collector Emitter Saturation Voltage vs. Collector Current (4401)

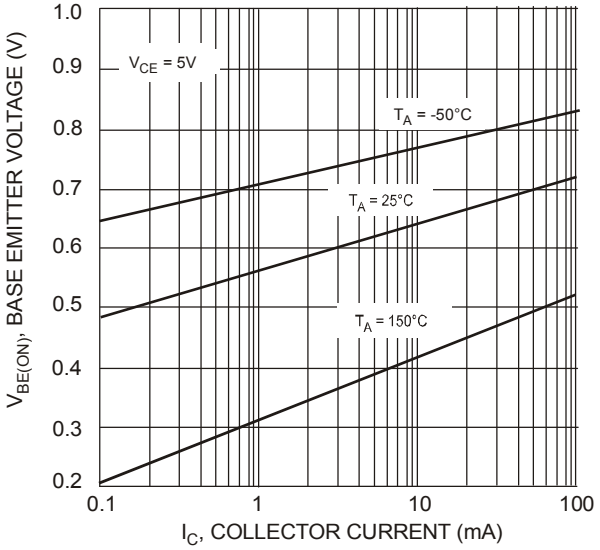


Fig. 5 Base Emitter Voltage vs. Collector Current (4401)

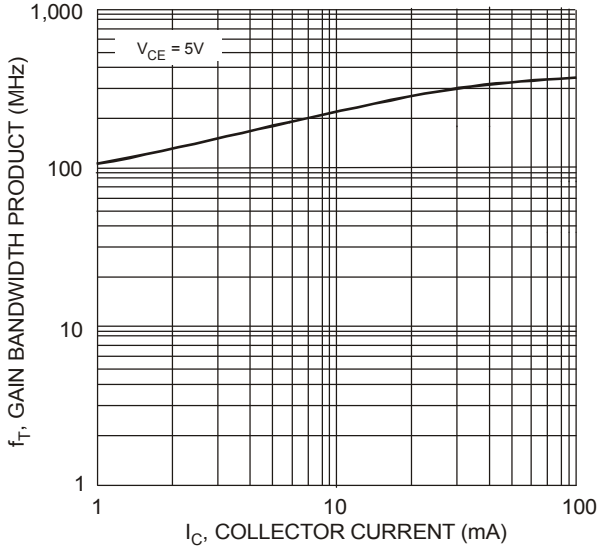


Fig. 6 Gain Bandwidth Product vs. Collector Current (4401)

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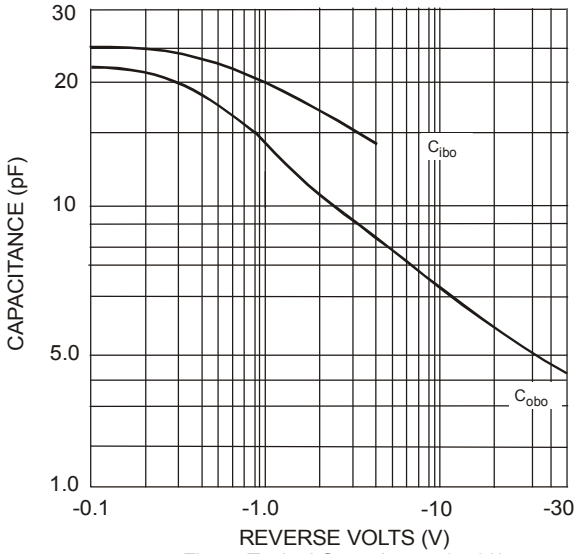


Fig. 7 Typical Capacitance (4403)

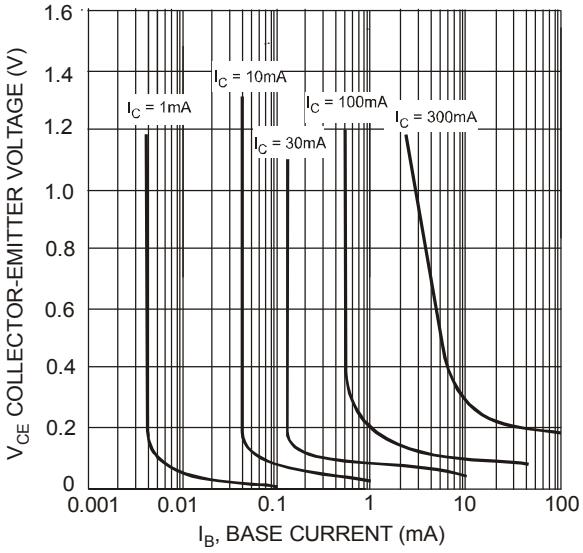


Fig. 8 Typical Collector Saturation Region (4403)

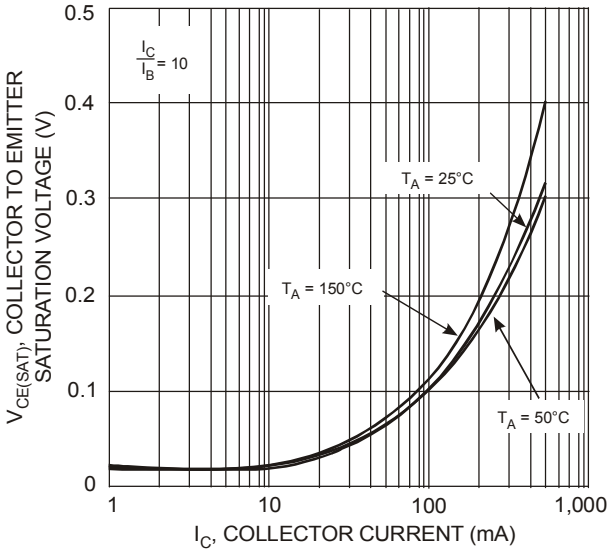


Fig. 9 Collector Emitter Saturation Voltage vs. Collector Current (4403)

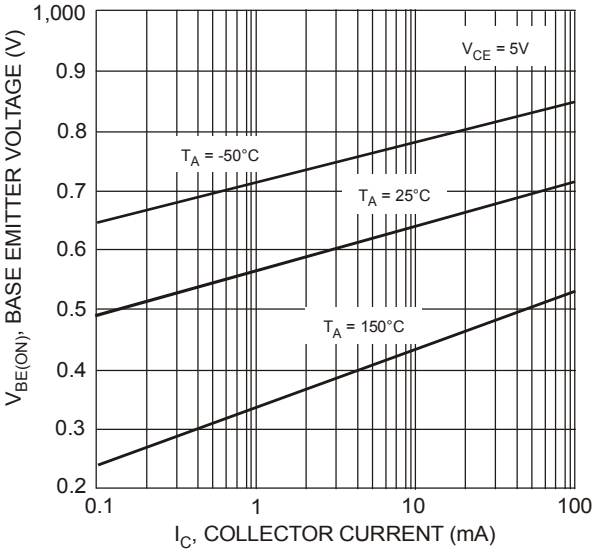


Fig. 10 Base-Emitter Voltage vs. Collector Current (4403)

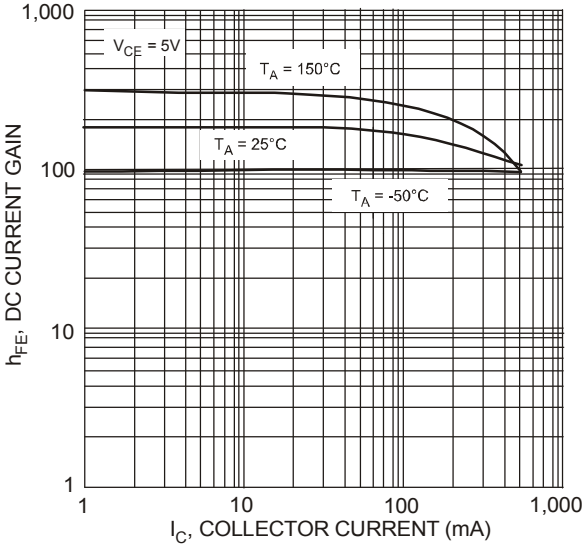


Fig. 11 DC Current Gain vs. Collector Current (4403)

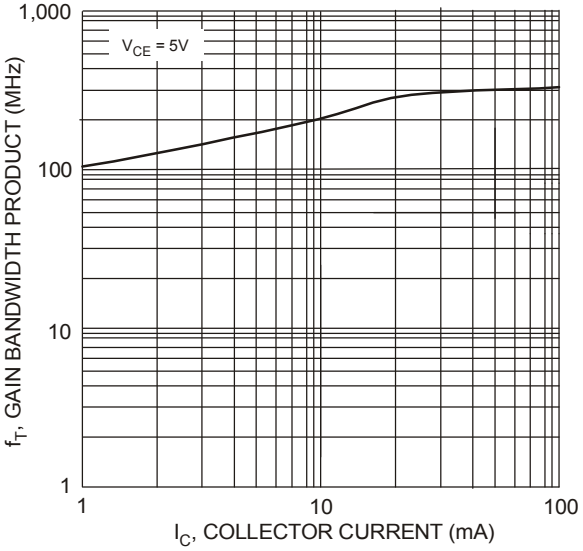


Fig. 12 Gain Bandwidth Product vs. Collector Current (4403)

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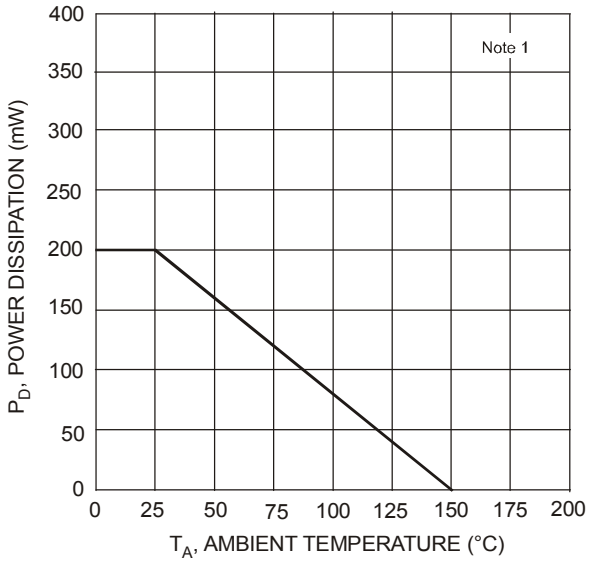


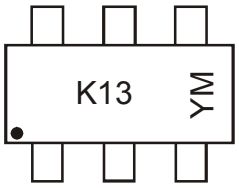
Fig. 13 Max Power Dissipation vs. Ambient Temperature (Total Device)

Ordering Information (Note 7)

Device	Packaging	Shipping
MMDT4413-7-F	SOT-363	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K13 = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Data Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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